

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("0644380").PN.	USPAT; USOCR	OR	OFF	2008/05/19 06:48
L2	1	("6544380").PN.	USPAT; USOCR	OR	OFF	2008/05/19 06:48
L3	18	("4539068" "4585516" "4863549" "5044311" "5057185" "5110438" "5116482" "5224202" "5246881" "5272417" "5277740" "5314603" "5330606" "5332880" "5460708" "5665167" "5711816" "RE30244").PN.	USPAT	OR	OFF	2008/05/19 06:51
L4	44954	(wafer or semiconductor or substrate) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower\$4) and ((side or sidewall or sideway or radial\$4) same (exhaust\$3 or outlet or eject\$3 or discharg\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 06:54
L5	22916	(wafer or semiconductor or substrate) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower\$4) and ((side or sidewall or sideway or radial\$4) near10 (exhaust\$3 or outlet or eject\$3 or discharg\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 06:55

L6	10715	((wafer or semiconductor or substrate) same (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)) and (plate or shower\$4) and ((side or sidewall or sideway or radial\$4) near10 (exhaust\$3 or outlet or eject\$3 or discharg\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 06:56
L7	4823	((wafer or semiconductor or substrate) same (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)) and (((hole or aperture or nozzle) with plate) or shower\$4) and ((side or sidewall or sideway or radial\$4) near10 (exhaust\$3 or outlet or eject\$3 or discharg\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 06:56
L8	1043	((wafer or semiconductor or substrate) same (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)) and (((hole or aperture or nozzle) with plate) or shower\$4) and (((wall near3 side) or sidewall or (vertical\$3 with wall)) near10 (exhaust \$3 or outlet or eject\$3 or discharg\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 06:57
L9	18	("4994301").URPN.	USPAT	OR	OFF	2008/05/19 07:16

L10	792	((wafer or semiconductor or substrate) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)) and (((hole or aperture or nozzle) with plate) or shower\$4) and (((wall near3 side) or sidewall or (vertical\$3 with wall)) near10 (exhaust \$3 or outlet or eject\$3 or discharg\$3)) and (dry\$3 or dried or supercritical)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 07:39
L11	0	((wafer or semiconductor or substrate) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)) and (((hole or aperture or nozzle) with plate) or shower\$4) and (((wall near3 side) or sidewall or (vertical\$3 with wall)) near10 (exhaust \$3 or outlet or eject\$3 or discharg\$3)) and (dry\$3 or dried or supercritical)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 07:42
L12	78	((wafer or semiconductor or substrate) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)) and (((hole or aperture or nozzle) with plate) or shower\$4) and ((wall near3 side) or sidewall or (vertical\$3 with wall))	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 07:43

L13	27	((wafer or semiconductor or substrate) and (dry\$3 or dried)).ab. and (((hole or aperture or nozzle) with plate) or shower\$4) and ((wall near3 side) or sidewall or (vertical\$3 with wall))	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 07:44
L14	1019	((wafer or semiconductor or substrate) and (dry\$3 or dried)).ab. and (((hole or aperture or nozzle) with plate) or shower\$4)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 07:45
L15	589	((wafer or semiconductor or substrate) with (dry\$3 or dried)).ab. and (((hole or aperture or nozzle) with plate) or shower\$4)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 07:45
L16	565	((wafer or semiconductor or substrate) with (dry\$3 or dried)).ab. and (((hole or aperture or nozzle) with plate) or shower\$4).ab.	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 07:45
L17	0	("62511123").PN.	USPAT; USOCR; JPO	OR	OFF	2008/05/19 08:45
L18	1	("6251223").PN.	USPAT; USOCR; JPO	OR	OFF	2008/05/19 08:45
L19	1	("62051223").PN.	USPAT; USOCR; JPO	OR	OFF	2008/05/19 08:46
L20	190	((wafer or semiconductor or substrate) and (dry\$3 or dried or gas or gases or (supercritical))).ab. and (((hole or aperture or nozzle) with plate) or shower\$4) and ((wall near3 side) or sidewall or (vertical\$3 with wall))	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 08:48

L21	4583	((wafer or semiconductor or substrate) and (dry\$3 or dried or gas or gases or (supercritical))).ab. and (((hole or aperture or nozzle) with plate) or shower\$4)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 08:48
L22	3001	((wafer or semiconductor or substrate) with (dry\$3 or dried or gas or gases or supercritical)).ab. and (((hole or aperture or nozzle) with plate) or shower\$4)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 08:49
L24	51	((wall near3 side) or sidewall or (vertical\$3 with wall)) near10 (exhaust\$3 or outlet or eject\$3 or discharg\$3)) and (((wafer or semiconductor or substrate) with (dry\$3 or dried or gas or gases or supercritical)) with (((hole or aperture or nozzle) with plate) or shower\$4)).ab.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 08:50
L25	2	("6656838").URPN.	USPAT	OR	OFF	2008/05/19 08:54
L26	7	("5863598" "6090210" "6100149" "6287635" "6403479").PN. OR ("6656838").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/19 08:54
S31	587	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and ((supercritical or subcritical) with ((carbon near2 dioxide) or (CO2)) with pressure) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/14 13:55

		turn or turning)				
S32	4484	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and ((supercritical or subcritical or pressure) with ((carbon near2 dioxide) or (CO2))) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/14 13:56
S33	2821	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and ((supercritical or subcritical or pressure) with ((carbon near2 dioxide) or (CO2))) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower or nozzle)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/14 13:56
S34	22976	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and ((supercritical or subcritical or pressure) with ((carbon near2 dioxide) or (CO2) or fluid)) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower or nozzle)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/14 13:57

S35	1326	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and ((supercritical or subcritical) with ((carbon near2 dioxide) or (CO2))) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower or nozzle)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/14 13:58
S36	147	("0002001" "0002002" "0002002" "0002003" "0002003" "0002004" "0002004" "20010013355" "20010013355" "20010017146" "20010027797" "20010047810" "20020011257" "20020025760" "20020043893" "20020086620" "20020086622" "20020088478" "20020108631" "20020115024" "20020115025" "20020139390" "20020144708" "20020153806" "20020157685" "20020157686" "20020173156" "20020173166" "20020195133" "20030024547" "20030028287" "20030061675" "20030062071" "20030064586" "20030088995" "20030106566" "20030106572" "20030106846" "20030111092"	US-PGPUB; USPAT	OR	ON	2008/05/14 14:06

"20030116174"	
"20030116176"	
"20030116491"	
"20030133851"	
"20030134518"	
"20030136334"	
"20030136422"	
"20030136429"	
"20030139057"	
"20030141784"	
"20030183246"	
"20030192571"	
"20030196679"	
"20030200986"	
"20030205240"	
"20030205559"	
"20030234029"	
"20040007257"	
"20040009740"	
"20040016442"	
"20040020512"	
"20040020781"	
"20040020898"	
"20040025911"	
"20040053503"	
"20040055621"	
"20040061199"	
"20040062874"	
"20040067639"	
"20040069319"	
"20040072448"	
"20040074521"	
"20040077172"	
"20040084318"	
"20040103919"	
"20040149308"	
"20040152319"	
"20040168706"	
"20040178476"	
"3973152" "3983515"	
"4326553"	
"4336719" "4373401"	
"4602184"	
"4836684" "4979994"	
"5013366"	
"5037481" "5090432"	
"5148823"	
"5203798" "5279316"	
"5337446"	
"5379785" "5379785"	
"5462604"	
"5497662" "5560362"	
"5625249"	
"5734588" "5865894"	
"5894092"	

		"5927308" "5927308" "5931173" "5932044" "5932077" "6016821" "6021789" "6026832" "6039059" "6041799" "6041938" "6098643" "6119367" "6136724" "6138694" "6138698" "6140744" "6148833" "6153533" "6209555" "6220259" "6241162" "6269511" "6273100" "6276370" "6276370" "6295999" "6314974" "6343609" "6385805" "6385809" "6395096" "6398937" "6412499" "6460551" "6460551" "6463938" "6513365" "6523557" "6523557" "6539952" "6554003" "6554003" "6554688" "6582525" "6585898" "6591845" "6595224" "6599402" "6619301" "6619305" "6745494" "6880560" "6904637" "7004016").PN.				
S37	6704	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower or nozzle)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/16 13:18

S38	6719	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower\$4 or nozzle)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/16 13:18
S39	3678	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower\$4)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/16 13:19
S40	951	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower\$4) and (side or sidewall or sideway or radial\$4)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/16 13:21
S41	131	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (high with pressure) and (plate or shower\$4) and (side or sidewall or sideway or radial\$4)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/18 23:52
S42	0	"200087296"	JPO	OR	ON	2008/05/19 00:59

S43	0	("200087296").PN.	JPO	OR	OFF	2008/05/19 00:59
S44	1	("200087296").PN.	JPO	OR	OFF	2008/05/19 00:59
S45	11	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (high with pressure) and (plate or shower\$4) and (sidewall)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:01
S46	653	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (plate or shower\$4) and (sidewall)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:02
S47	11	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (plate or shower\$4) and (sidewall with (discharge or outlet))	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:03
S48	84	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (sidewall with (discharge or outlet))	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:04
S49	1398	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (sidewall with (discharge or outlet))	US-PGPUB; USPAT; USOCR	OR	ON	2008/05/19 01:07

S50	439	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (sidewall near3 (discharge or outlet))	US-PGPUB; USPAT; USOCR	OR	ON	2008/05/19 01:08
S51	282	((wafer or semiconductor or substrate) with (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing)) and (sidewall near3 (discharge or outlet))	US-PGPUB; USPAT; USOCR	OR	ON	2008/05/19 01:08
S52	34	((wafer or semiconductor or substrate) with (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing)) and (sidewall near3 (discharge or outlet)). ab.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:10
S53	653	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (plate or shower\$4) and (sidewall)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:16
S54	309	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (plate or shower\$4) and ((sidewall or (side near2 wall)) with (opening or aperture or outlet or hole or discharg\$4))	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:19

S55	1	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (plate or shower\$4) and ((sidewall or (side near2 wall)) with (opening or aperture or outlet or hole or discharg\$4)) and (high near2 pressure)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:19
S56	12	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (plate or shower\$4) and ((sidewall or (side near2 wall)) with (opening or aperture or outlet or hole or discharg\$4)) and (supercritical or dioxide)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:20
S57	2	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (shower\$4) and ((sidewall or (side near2 wall)) with (opening or aperture or outlet or hole or discharg\$4))	FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:21

S58	1011	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (shower\$4) and ((sidewall or (side near2 wall)) with (opening or aperture or outlet or hole or discharg\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:21
S59	24224	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((sidewall or (side near2 wall)) with (opening or aperture or outlet or hole or discharg\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:22
S60	704	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((shower\$4 or plate) with (turbulence or turbulent))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:40

S61	653	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((shower\$4 or plate) with (turbulence or turbulent)) and (side or sidewall or sideway or radial\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:41
S62	34	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (shower\$4 with (turbulence or turbulent)) and (side or sidewall or sideway or radial\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:42
S63	1	("6723224").URPN.	USPAT	OR	OFF	2008/05/19 01:46
S64	653	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((plate or shower\$4) with (turbulence or turbulent)) and (side or sidewall or sideway or radial\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:48

S65	130	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((plate or shower\$4) with (turbulence or turbulent)) and ((side or sidewall or sideway or radial\$4) with (eject \$3 or discharg\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:48
S66	204	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((plate or shower\$4) with (turbulence or turbulent)) and ((side or sidewall or sideway or radial\$4) with (eject \$3 or discharg\$3 or outlet))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:48
S67	103	(wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((plate or shower\$4) with (turbulence or turbulent)) and ((side or sidewall or sideway or radial\$4) with (eject \$3 or discharg\$3 or outlet)) and ((high with pressure) or	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 01:49

S71	637	((wafer or semiconductor or substrate) and (dry\$3 or dried)).ab. and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower\$4) and ((side or sidewall or sideways or radial\$4) same (exhaust\$3 or outlet or eject\$3 or discharg\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 02:14
S72	6	hitachi.as. and plate and dried and (spin adj chuck)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 02:23
S73	0	("4271882").PN.	JPO	OR	OFF	2008/05/19 02:33
S74	0	("40271882").PN.	JPO	OR	OFF	2008/05/19 02:33
S75	897	hitachi.as. and amada.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 02:39
S76	152	hitachi.as. and amada.in. and (wafer or substrate or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/05/19 02:39

5/19/2008 8:56:51 AM

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